

# FDN361AN

### N-Channel, Logic Level, PowerTrench™

### **General Description**

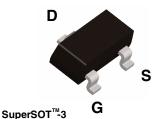
This N-Channel Logic Level MOSFET is produced using Fairchild Semiconductor's PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

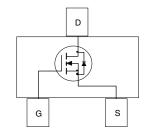
### **Applications**

- DC/DC converter
- Load switch
- Motor drives

### **Features**

- 1.8 A, 30 V.  $R_{DS(on)} = 0.100~\Omega~$  @  $V_{GS} = 10~V$   $R_{DS(on)} = 0.150~\Omega~$  @  $V_{GS} = 4.5~V.$
- Low gate charge (2.1nC typical).
- Fast switching speed.
- High performance trench technology for extremely low R<sub>DS(on)</sub>.
- High power version of industry standard SOT-23 package. Identical pin out to SOT-23 with 30% higher power handling capability.





Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter		FDN361AN	Units
$V_{DSS}$	Drain-Source Voltage		30	V
$V_{GSS}$	Gate-Source Voltage - Continuous	±20	V	
I <sub>D</sub>	Drain Current - Continuous	(Note 1a)	1.8	А
	- Pulsed		8	
P <sub>D</sub>	Power Dissipation for Single Operation	(Note 1a)	0.5	W
		(Note 1b)	0.46	
TJ, Tsta	Operating and Storage Junction Temperat	-55 to +150	°C	

### **Thermal Characteristics**

$R_{\theta^{JA}}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	250	°C/W
R <sub>AJC</sub>	Thermal Resistance, Junction-to-Case	(Note 1)	75	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
361	FDN361AN	7"	8mm	3000 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Cha	racteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V
_ABVdss ΔTJ	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		24		mV/∘C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA
I <sub>GSSF</sub>	Gate-Body Leakage, Forward	V <sub>GS</sub> = 20 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage, Reverse	V <sub>GS</sub> = -20 V, V <sub>DS</sub> = 0 V			-100	nA
On Char	acteristics (Note 2)				1	
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	1	1.8	3	V
<u>A</u> VGS(th) ΔTJ	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \mu A$ , Referenced to 25°C		-4.2		mV/∘C
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 1.8 \text{ A}$ $V_{GS} = 10 \text{ V}, I_D = 1.8 \text{ A}, T_J = 125 ^{\circ}\text{C}$ $V_{GS} = 4.5 \text{ V}, I_D = 1.4 \text{ A}$		0.072 0.107 0.105	0.1 0.16 0.15	Ω
I <sub>D(on)</sub>	On-State Drain Current	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 5 V	8			Α
<b>g</b> <sub>FS</sub>	Forward Transconductance	$V_{DS} = 10 \text{ V}, I_{D} = 1.8 \text{ A}$		5		S
Dynamic	Characteristics					
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz		220		pF
Coss	Output Capacitance			50		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			20		pF
Switchin	g Characteristics (Note 2)					
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 15 \text{ V}, I_D = 1 \text{ A},$		3	6	ns
t	Turn-On Rise Time	On Rise Time $V_{GS} = 10 \text{ V}, R_{GEN} = 6.0 \Omega$		11	22	ns
$t_{\text{d(off)}} \\$	Turn-Off Delay Time			7	14	ns
$t_f$	Turn-Off Fall Time			3	6	ns
$Q_g$	Total Gate Charge	$V_{DS} = 15 \text{ V}, I_D = 1.8 \text{ A},$		2.1	4	nC
$Q_{gs}$	Gate-Source Charge	$V_{GS} = 5 V$		0.8		nC
$Q_{gd}$	Gate-Drain Charge			0.7		nC
Drain-Sc	ource Diode Characteristics	and Maximum Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Sour	ce Diode Forward Current			0.42	Α
V <sub>SD</sub>	Drain-Source Diode Forward	$V_{GS} = 0 \text{ V}, I_S = 0.42 \text{ A}$ (Note 2)		0.75	1.2	V

### Notes:

 R<sub>BJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>BJC</sub> is guaranteed by design while R<sub>BJA</sub> is determined by the user's board design.



a)  $250^{\circ}\text{C/W}$  when mounted on a 0.02 in<sup>2</sup> pad of 2 oz. Cu.



b) 270°C/W when mounted on a mininum pad.

Scale 1 : 1 on letter size paper

Voltage

2. Pulse Test: Pulse Width  $\leq 300~\mu s,~\text{Duty Cycle} \leq 2.0\%$ 

## Typical Characteristics (continued)

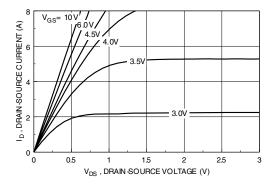


Figure 1. On-Region Characteristics.

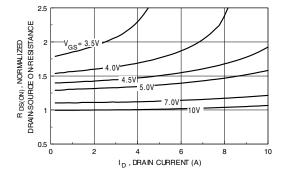


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

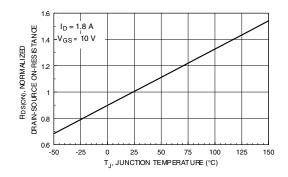


Figure 3. On-Resistance Variation with Temperature.

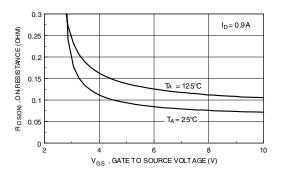


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

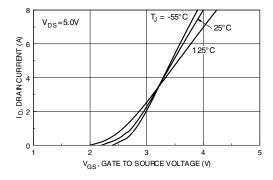


Figure 5. Transfer Characteristics.

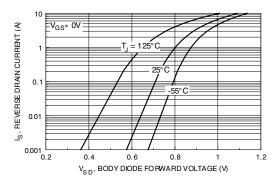
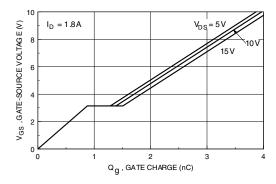


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

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### Typical Characteristics (continued)



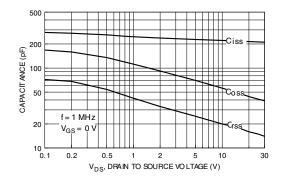
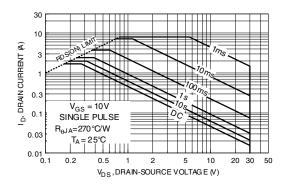


Figure 7. Gate-Charge Characteristics.





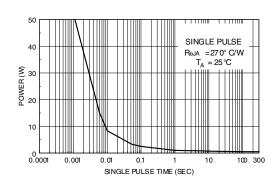


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

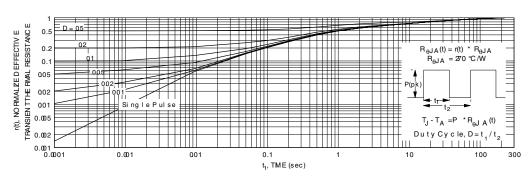
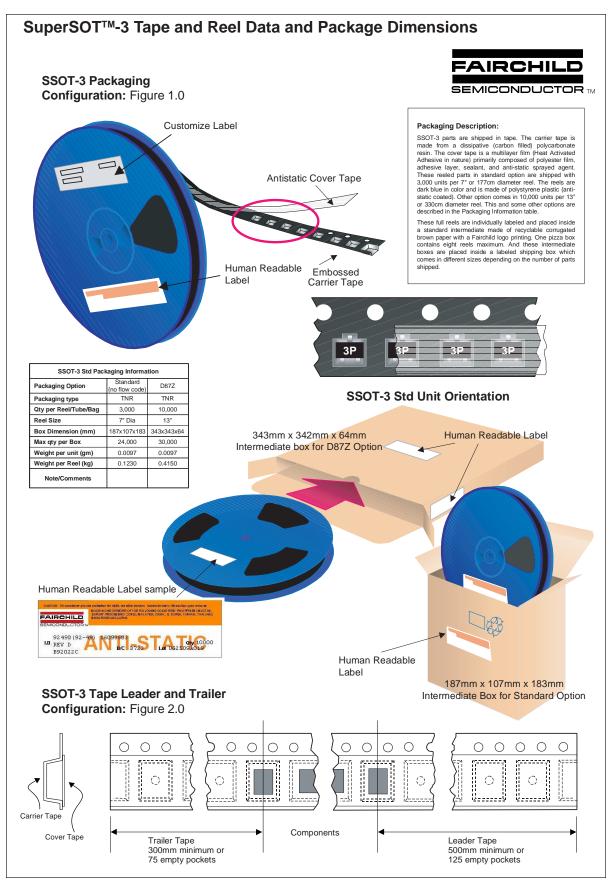
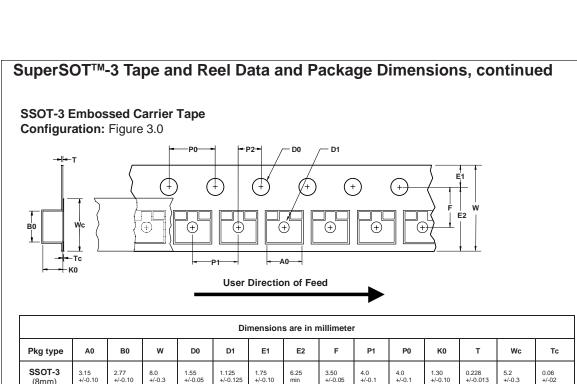


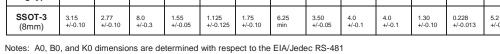
Figure 11. Transient Thermal Response Curve.

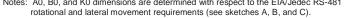
Thermal characterization performed using the conditions described in Note 1b. Transient themal response will change depending on the circuit board design.

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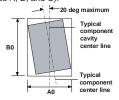




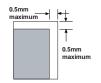




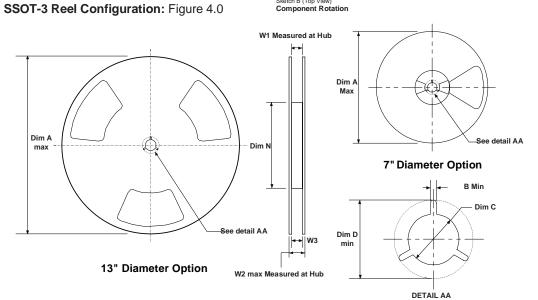
Sketch A (Side or Front Sectional View)
Component Rotation



Sketch B (Top View)
Component Rotation



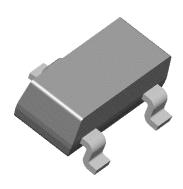
Sketch C (Top View)
Component lateral movement

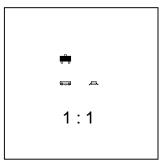


Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

# SuperSOT™-3 Tape and Reel Data and Package Dimensions, continued

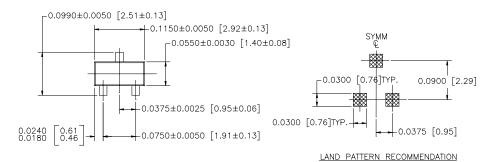
# SuperSOT™-3 (FS PKG Code 32)

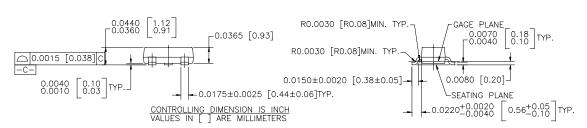




Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0097





NOTES: UNLESS OTHERWISE SPECIFIED

SUPER SOT , 3 LEADS

- 1. STANDARD LEAD FINISH TO BE 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN/LEAD (SOLDER) ON COPPER.
- 2. NO JEDEC REGISTRATION AS OF DEC. 1995.

September 1998, Rev. A

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Rev. D